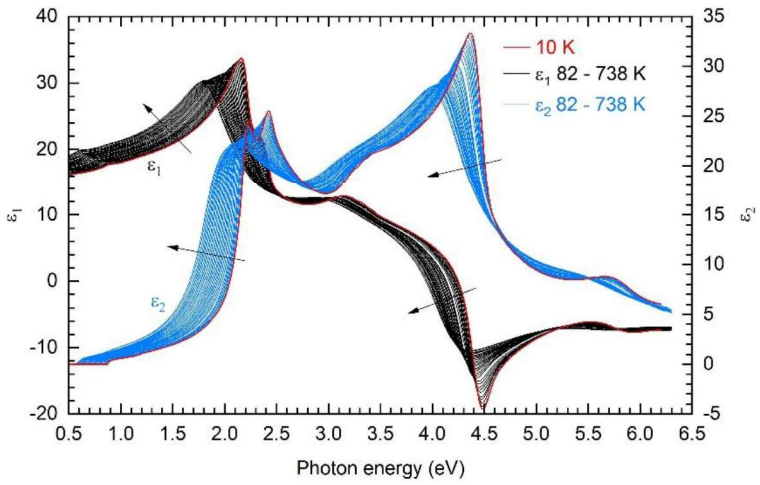

Figure 1: Temperature dependence of the real and imaginary parts of the dielectric function of bulk Ge from 10 K (red) to 738 K. The arrows indicate the temperature direction.

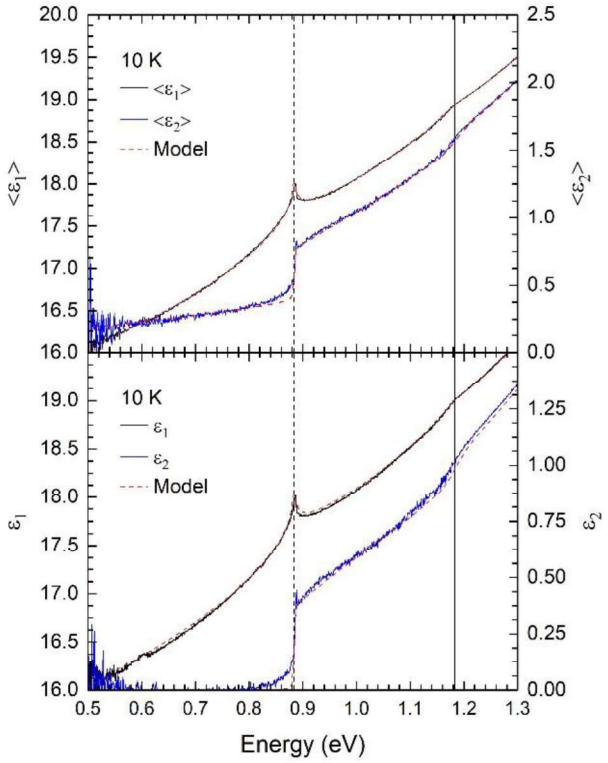

Figure 2 (above): Pseudo-dielectric (top) and dielectric function (bottom) of Ge at 10 K showing the E_0 and $E_0+\Delta_0$ critical points. The dashed line corresponds to the energy of E_0 and the solid line to $E_0+\Delta_0$.

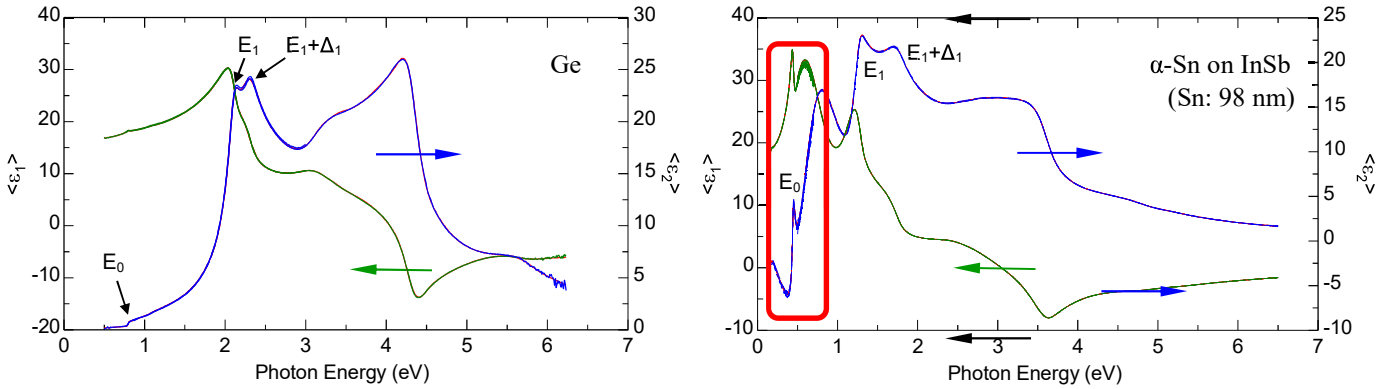

Figure 3: Pseudo-dielectric function of bulk Ge (left) and α-Sn on InSb (right) at room temperature. The peak in the infrared region of the spectrum of Sn is significantly larger than the absorption edge of Ge at 0.8 eV.